

Amendments to the Claims:

Please amend claims 21, 22, 24, 29, 31, 33, 34 and 39. Please add new claims 41 and 42.

The claims are as follows:

1-20 (Canceled)

21. (Currently Amended) An electrical structure, comprising:

a parent terrain denoted as V_0 ; and

N voltage islands denoted as V_1 , V_2, \dots, V_N ~~nested within said parent terrain, N at least 2, voltage island V_Z nested within a voltage island V_{Z-1} for $Z=1, 2, \dots, N$ said voltage island V_1 nested within said parent terrain V_0 and said voltage island V_2 nested within said voltage island V_1 .~~

22. (Currently Amended) The electrical structure of claim ~~[[21]]~~ 41, wherein each voltage island of the N voltage islands includes one or more voltage power supplies selected from the group consisting of an internal voltage island VDDI power supply, an externally supplied state saving VDDSS power supply, an externally supplied VDDN power supply, and combinations thereof.

23. (Previously Presented) The electrical structure of claim 22, wherein said one or more power supplies of voltage island V_X for $X=1, 2, \dots, N$ are each independently coupled to one of (a) said one or more power supplies of voltage island V_Y , for $Y=1, 2, \dots, N$, X not equal to Y , (b) a VDDO power supply of said parent terrain or (c) one or more external to said parent terrain power supplies.

24. (Currently Amended) The electrical structure of claim ~~[[21]]~~ 41, wherein each voltage island of the N voltage islands includes (a) an externally supplied VDDN power supply and a voltage shifting means, or (b) said externally supplied VDDN power supply and a fencing means, or (c) said externally supplied VDDN power supply, said voltage shifting means and said fencing means.

25. (Previously Presented) The electrical structure of claim 24, wherein said fencing means comprises logic latches.

26. (Previously Presented) The electrical structure of claim 24, wherein each voltage island of the N voltage islands further includes one or more substructures selected from the group consisting of (a) an internal voltage island VDDI power distribution network, (b) state saving means, (c) one or more switching elements coupled between said externally supplied VDDN power supply and said internal voltage island VDDI power distribution network, and (d) one or more voltage buffering circuits.

27. (Previously Presented) The electrical structure of claim 26, wherein said one or more switching elements is selected from the group consisting of hard connections, voltage regulators, headers and footers.

28. (Previously Presented) The electrical structure of claim 26, wherein said state saving means includes at least one state saving latch.

29. (Currently Amended) The electrical structure of claim [[21]] 41, wherein one or more voltage islands of the N voltage islands further includes a power management state machine coupled to an internal voltage island VDDI power supply distribution network, said power management state machine of voltage island V_X for $X=1, 2, \dots, N$ located in (a) voltage island V_Y for $Y=1, 2, \dots, N$, Y less than X , or (b) in said parent terrain.

30. (Previously Presented) The electrical structure of claim 21, wherein said parent terrain is an integrated circuit chip or a voltage island within said integrated circuit chip.

31. (Currently Amended) A method, comprising:

providing a parent terrain denoted as V_0 ; and

~~nesting N voltage islands denoted as V_1, V_2, \dots, V_N within said parent terrain, N at least 2,~~
~~voltage island V_Z nested within a voltage island V_{Z+1} for $Z=1, 2, \dots, N$ nesting a voltage island V_1~~
~~within said parent terrain V_0 and nesting a voltage island V_2 within said voltage island V_1 .~~

32. (Currently Amended) The method of claim [[31]] 42, wherein each voltage island of the N voltage islands includes one or more voltage power supplies selected from the group consisting of an internal voltage island VDDI power supply, an externally supplied state saving VDDSS power supply, an externally supplied VDDN power supply, and combinations thereof.

33. (Currently Amended) The electrical structure of claim [[31]] 42, wherein said one or more power supplies of voltage island V_X for $X=1, 2, \dots, N$ are each independently coupled to one of (a) said one or more power supplies of voltage island V_Y , for $Y=1, 2, \dots, N$, X not equal to Y , (b)

a VDDO power supply of said parent terrain or (c) one or more external to said parent terrain power supplies.

34. (Previously Presented) The method of claim 31, wherein each voltage island of the N voltage islands includes (a) an externally supplied VDDN power supply and a voltage shifting means, or (b) said externally supplied VDDN power supply and a fencing means, or (c) said externally supplied VDDN power supply, said voltage shifting means and said fencing means.

35. (Previously Presented) The method of claim 34, wherein said fencing means comprises logic latches.

36. (Previously Presented) The method of claim 34, wherein each voltage island of the N voltage islands further includes one or more substructures selected from the group consisting of (a) an internal voltage island VDDI power distribution network, (b) state saving means, (c) one or more switching elements coupled between said externally supplied VDDN power supply and said internal voltage island VDDI power distribution network, and (d) one or more voltage buffering circuits.

37. (Previously Presented) The method of claim 36, wherein said one or more switching elements is selected from the group consisting of hard connections, voltage regulators, headers and footers.

38. (Previously Presented) The method of claim 36, wherein said state saving means includes at least one state saving latch.

39. (Currently Amended) The electrical structure of claim [[31]] 42, wherein one or more voltage islands of the N voltage islands further includes a power management state machine coupled to an internal voltage island VDDI power supply distribution network, said power management state machine of voltage island V_X for $X=1, 2, \dots, N$ located in (a) a voltage island V_Y for $Y=1, 2, \dots, N$, Y less than X , or (b) in said parent terrain.

40. (Previously Presented) The method of claim 31, wherein said parent terrain is an integrated circuit chip or a voltage island within said integrated circuit chip.

41. (New) The electrical structure of claim 21, further including:

additional voltage islands denoted as V_3, V_4, \dots, V_N , a voltage island V_Z nested within a voltage island V_{Z-1} for $Z=3, 4, \dots, N$, wherein N is an integer of at least 3.

42. (New) The method of claim 21, further including:

providing additional voltage islands denoted as V_3, V_4, \dots, V_N ; and
nesting a voltage island V_Z within a voltage island V_{Z-1} for $Z=3, 4, \dots, N$, wherein N is an integer of at least 3.